



## TS5A23157 Dual 10-Ω SPDT Analog Switch

### 1 Features

- Low ON-State Resistance (10 Ω)
- Control Inputs are 5-V Tolerant
- Specified Break-Before-Make Switching
- Low Charge Injection
- Excellent ON-Resistance Matching
- Low Total Harmonic Distortion
- 1.8-V to 5.5-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)

### 2 Applications

- Sample-and-Hold Circuits
- Battery-Powered Equipment
- Audio and Video Signal Routing
- Communication Circuits

### 3 Description

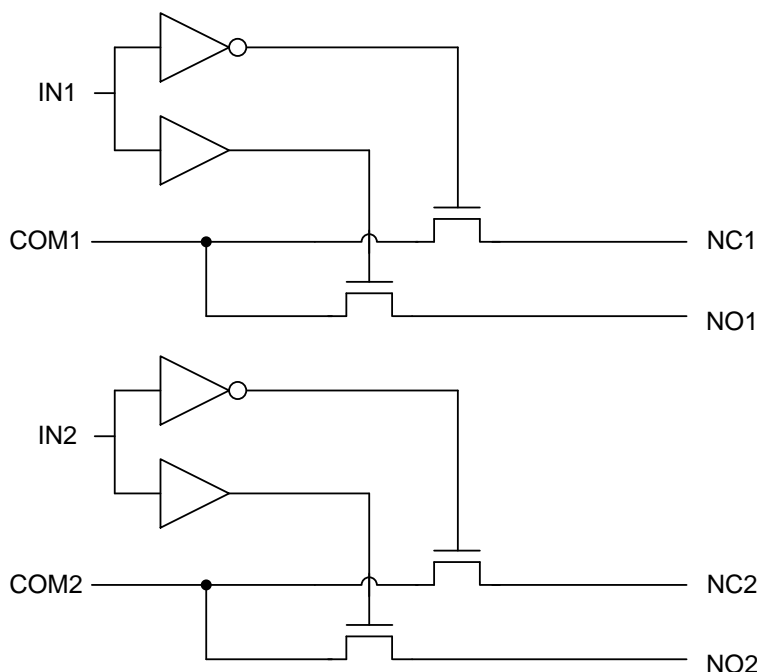
The TS5A23157 device is a dual single-pole double-throw (SPDT) analog switch designed to operate from 1.65 V to 5.5 V. This device can handle both digital and analog signals. Signals up to 5.5 V (peak) can be transmitted in either direction.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TS5A23157DGS	VSSOP (10)	3.00 mm × 3.00 mm
TS5A23157RSE	UQFN (10)	2.00 mm × 1.50 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

**Block Diagram**



## Table of Contents

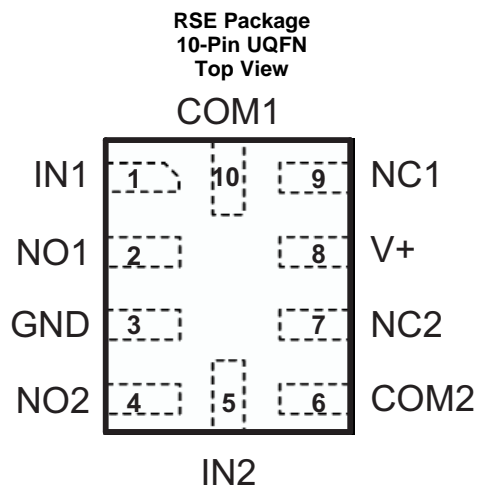
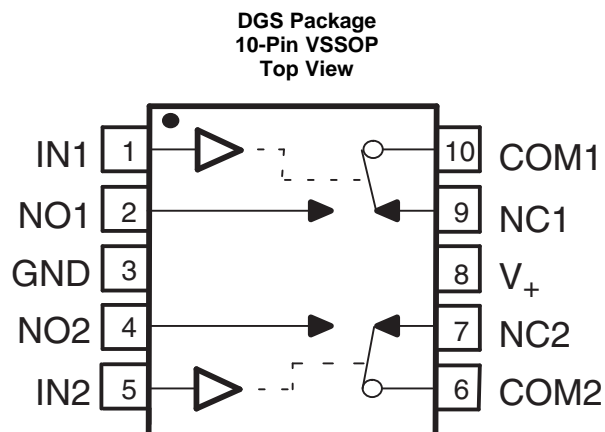
<b>1 Features</b> .....	<b>1</b>	8.2 Functional Block Diagram .....	<b>16</b>
<b>2 Applications</b> .....	<b>1</b>	8.3 Feature Description .....	<b>16</b>
<b>3 Description</b> .....	<b>1</b>	8.4 Device Functional Modes .....	<b>16</b>
<b>4 Revision History</b> .....	<b>2</b>	<b>9 Application and Implementation</b> .....	<b>17</b>
<b>5 Pin Configuration and Functions</b> .....	<b>3</b>	9.1 Application Information .....	<b>17</b>
<b>6 Specifications</b> .....	<b>4</b>	9.2 Typical Application .....	<b>17</b>
6.1 Absolute Maximum Ratings .....	<b>4</b>	<b>10 Power Supply Recommendations</b> .....	<b>18</b>
6.2 ESD Ratings .....	<b>4</b>	<b>11 Layout</b> .....	<b>18</b>
6.3 Recommended Operating Conditions .....	<b>4</b>	11.1 Layout Guidelines .....	<b>18</b>
6.4 Thermal Information .....	<b>4</b>	11.2 Layout Example .....	<b>19</b>
6.5 Electrical Characteristics for 5-V Supply .....	<b>5</b>	<b>12 Device and Documentation Support</b> .....	<b>19</b>
6.6 Electrical Characteristics for 3.3-V Supply .....	<b>6</b>	12.1 Device Support .....	<b>19</b>
6.7 Electrical Characteristics for 2.5-V Supply .....	<b>7</b>	12.2 Documentation Support .....	<b>21</b>
6.8 Electrical Characteristics for 1.8-V Supply .....	<b>8</b>	12.3 Community Resources .....	<b>21</b>
6.9 Typical Characteristics .....	<b>10</b>	12.4 Trademarks .....	<b>21</b>
<b>7 Parameter Measurement Information</b> .....	<b>12</b>	12.5 Electrostatic Discharge Caution .....	<b>21</b>
<b>8 Detailed Description</b> .....	<b>16</b>	12.6 Glossary .....	<b>21</b>
8.1 Overview .....	<b>16</b>	<b>13 Mechanical, Packaging, and Orderable Information</b> .....	<b>21</b>

## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (October 2013) to Revision E	Page
<ul style="list-style-type: none"> <li>Added <i>Pin Configuration and Functions</i> section, <i>ESD Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i>, <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section .....</li> </ul>	<b>1</b>

## 5 Pin Configuration and Functions



### Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	IN1	I	Select pin for switch 1
2	NO1	I/O	Normally open I/O for switch 1
3	GND	—	Ground
4	NO2	I/O	Normally open I/O for switch 2
5	IN2	I	Select pin for switch 2
6	COM2	I/O	Common I/O for switch 2
7	NC2	I/O	Normally closed I/O for switch 2
8	V+	—	Power supply pin
9	NC1	I/O	Normally closed I/O for switch 1
10	COM1	I/O	Common I/O for switch 1

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>+</sub>	Supply voltage <sup>(2)</sup>		−0.5	6.5	V
V <sub>NC</sub> V <sub>NO</sub> V <sub>COM</sub>	Analog voltage <sup>(2)(3)(4)</sup>		−0.5	V <sub>+</sub> + 0.5	V
I <sub>I/OK</sub>	Analog port diode current	V <sub>NC</sub> , V <sub>NO</sub> , V <sub>COM</sub> < 0 or V <sub>NC</sub> , V <sub>NO</sub> , V <sub>COM</sub> > V <sub>+</sub>	±50		mA
I <sub>NC</sub> I <sub>NO</sub> I <sub>COM</sub>	On-state switch current	V <sub>NC</sub> , V <sub>NO</sub> , V <sub>COM</sub> = 0 to V <sub>+</sub>	±50		mA
V <sub>IN</sub>	Digital input voltage <sup>(2)(3)</sup>		−0.5	6.5	V
I <sub>IK</sub>	Digital input clamp current	V <sub>IN</sub> < 0	−50		mA
Continuous current through V <sub>+</sub> or GND			±100		mA
T <sub>stg</sub>	Storage temperature		−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground, unless otherwise specified.
- (3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (4) This value is limited to 5.5 V maximum.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V <sub>I/O</sub>	Switch input/output voltage	0	V <sub>+</sub>	V
V <sub>+</sub>	Supply voltage	1.65	5.5	V
V <sub>I</sub>	Control input voltage	0	5.5	V
T <sub>A</sub>	Operating temperature	−40	85	°C

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TS5A23157		UNIT
		DGS (VSSOP)	RSE (UQFN)	
		10 PINS	10 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	56.5	243	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Electrical Characteristics for 5-V Supply

 $V_+ = 4.5 \text{ V to } 5.5 \text{ V}$ ,  $T_A = -40^\circ\text{C to } 85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A$	$V_+$	MIN	TYP <sup>(1)</sup>	MAX	UNIT
<b>ANALOG SWITCH</b>							
$V_{COM}$ , $V_{NO}$ , $V_{NC}$	Analog signal range			0		$V_+$	V
$r_{on}$	ON-state resistance	$0 \leq V_{NO} \text{ or } V_{NC} \leq V_+$ , $I_{COM} = -30 \text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	Full	4.5 V		10	$\Omega$
$\Delta r_{on}$	ON-state resistance match between channels	$V_{NO} \text{ or } V_{NC} = 3.15 \text{ V}$ , $I_{COM} = -30 \text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	25°C	4.5 V	0.15		$\Omega$
$r_{on(Flat)}$	ON-state resistance flatness	$0 \leq V_{NO} \text{ or } V_{NC} \leq V_+$ , $I_{COM} = -30 \text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	25°C	4.5 V	4		$\Omega$
$I_{NC(OFF)}$ , $I_{NO(OFF)}$	NC, NO OFF leakage current	$V_{NC} \text{ or } V_{NO} = 0 \text{ to } V_+$ , $V_{COM} = 0 \text{ to } V_+$ , Switch OFF, see <a href="#">Figure 10</a>	25°C Full	5.5 V	-1 -1	0.05 1	$\mu\text{A}$
$I_{NC(ON)}$ , $I_{NO(ON)}$	NC, NO ON leakage current	$V_{NC} \text{ or } V_{NO} = 0 \text{ to } V_+$ , $V_{COM} = \text{Open}$ , Switch ON, see <a href="#">Figure 10</a>	25°C Full	5.5 V	-0.1 -1	0.1 1	$\mu\text{A}$
$I_{COM(ON)}$	COM ON leakage current	$V_{NC} \text{ or } V_{NO} = \text{Open}$ , $V_{COM} = 0 \text{ to } V_+$ , Switch ON, see <a href="#">Figure 10</a>	25°C Full	5.5 V	-0.1 -1	0.1 1	$\mu\text{A}$
<b>DIGITAL INPUTS (IN12, IN2)<sup>(2)</sup></b>							
$V_{IH}$	Input logic high		Full		$V_+ \times 0.7$		V
$V_{IL}$	Input logic low		Full		$V_+ \times 0.3$		V
$I_{IH}$ , $I_{IL}$	Input leakage current	$V_{IN} = 5.5 \text{ V or } 0$	25°C Full	5.5 V	-1 -1	0.05 1	$\mu\text{A}$
<b>DYNAMIC</b>							
$t_{ON}$	Turnon time	$V_{NC} = \text{GND and } V_{NO} = V_+$ or $V_{NC} = V_+ \text{ and } V_{NO} = \text{GND}$ , $R_L = 500 \Omega$ , $C_L = 50 \text{ pF}$ , see <a href="#">Figure 12</a>	Full	4.5 V to 5.5 V	1.7	5.7	ns
$t_{OFF}$	Turnoff time	$V_{NC} = \text{GND and } V_{NO} = V_+$ or $V_{NC} = V_+ \text{ and } V_{NO} = \text{GND}$ , $R_L = 500 \Omega$ , $C_L = 50 \text{ pF}$ , see <a href="#">Figure 12</a>	Full	4.5 V to 5.5 V	0.8	3.8	ns
$t_{BBM}$	Break-before-make time	$V_{NC} = V_{NO} = V_+/2$ , $R_L = 50 \Omega$ , $C_L = 35 \text{ pF}$ , see <a href="#">Figure 13</a>	Full	4.5 V to 5.5 V	0.5		ns
$Q_C$	Charge injection	$V_{NC} = V_{NO} = V_+/2$ , $R_L = 50 \Omega$ , See <a href="#">Figure 17</a>	25°C	5 V	7		pC
$C_{NC(OFF)}$ , $C_{NO(OFF)}$	NC, NO OFF capacitance	$V_{NC} \text{ or } V_{NO} = V_+ \text{ or GND}$ , Switch OFF, see <a href="#">Figure 11</a>	25°C	5 V	5.5		pF
$C_{NC(ON)}$ , $C_{NO(ON)}$	NC, NO ON capacitance	$V_{NC} \text{ or } V_{NO} = V_+ \text{ or GND}$ , Switch ON, see <a href="#">Figure 11</a>	25°C	5 V	17.5		pF
$C_{COM(ON)}$	COM ON capacitance	$V_{COM} = V_+ \text{ or GND}$ , Switch ON, see <a href="#">Figure 11</a>	25°C	5 V	17.5		pF
$C_{IN}$	Digital input capacitance	$V_{IN} = V_+ \text{ or GND}$ , See <a href="#">Figure 11</a>	25°C	5 V	2.8		pF
BW	Bandwidth	$R_L = 50 \Omega$ , Switch ON, see <a href="#">Figure 14</a>	25°C	4.5 V	220		MHz
$O_{ISO}$	OFF isolation	$R_L = 50 \Omega$ , $f = 10 \text{ MHz}$ , Switch OFF, see <a href="#">Figure 15</a>	25°C	4.5 V	-65		dB
$X_{TALK}$	Crosstalk	$R_L = 50 \Omega$ , $f = 10 \text{ MHz}$ , Switch ON, see <a href="#">Figure 16</a>	25°C	4.5 V	-66		dB
THD	Total harmonic distortion	$R_L = 600 \Omega$ , $C_L = 50 \text{ pF}$ , $f = 600 \text{ Hz to } 20 \text{ kHz}$ , see <a href="#">Figure 18</a>	25°C	4.5 V	0.01%		

(1)  $T_A = 25^\circ\text{C}$ .

(2) All unused digital inputs of the device must be held at  $V_+$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

## Electrical Characteristics for 5-V Supply (continued)

 $V_+ = 4.5 \text{ V to } 5.5 \text{ V}$ ,  $T_A = -40^\circ\text{C to } 85^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T <sub>A</sub>	V <sub>+</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
SUPPLY									
I <sub>+</sub>	Positive supply current	V <sub>IN</sub> = V <sub>+</sub> or GND,	Switch ON or OFF	25°C	5.5 V			1	μA
				Full				10	
ΔI <sub>+</sub>	Change in supply current	V <sub>IN</sub> = V <sub>+</sub> − 0.6 V		Full	5.5 V			500	μA

## 6.6 Electrical Characteristics for 3.3-V Supply

 $V_+ = 3 \text{ V to } 3.6 \text{ V}$ ,  $T_A = -40^\circ\text{C to } 85^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T <sub>A</sub>	V <sub>+</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
ANALOG SWITCH									
V <sub>COM</sub> , V <sub>NO</sub> , V <sub>NC</sub>	Analog signal range					0		V <sub>+</sub>	V
r <sub>on</sub>	ON-state resistance	0 ≤ V <sub>NO</sub> or V <sub>NC</sub> ≤ V <sub>+</sub> , I <sub>COM</sub> = −24 mA,	Switch ON, see <a href="#">Figure 9</a>	Full	3 V			18	Ω
Δr <sub>on</sub>	ON-state resistance match between channels	V <sub>NO</sub> or V <sub>NC</sub> = 2.1 V, I <sub>COM</sub> = −24 mA,	Switch ON, see <a href="#">Figure 9</a>	25°C	3 V		0.2		Ω
r <sub>on(flat)</sub>	ON-state resistance flatness	0 ≤ V <sub>NO</sub> or V <sub>NC</sub> ≤ V <sub>+</sub> , I <sub>COM</sub> = −24 mA,	Switch ON, see <a href="#">Figure 11</a>	25°C	3 V		9		Ω
I <sub>NC(OFF)</sub> , I <sub>NO(OFF)</sub>	NC, NO OFF leakage current	V <sub>NC</sub> or V <sub>NO</sub> = 0 to V <sub>+</sub> , V <sub>COM</sub> = 0 to V <sub>+</sub> ,	Switch OFF, see <a href="#">Figure 10</a>	25°C Full	3.6 V	−1 −1	0.05	1 1	μA
I <sub>NC(ON)</sub> , I <sub>NO(ON)</sub>	NC, NO ON leakage current	V <sub>NC</sub> or V <sub>NO</sub> = 0 to V <sub>+</sub> , V <sub>COM</sub> = Open,	Switch ON, see <a href="#">Figure 10</a>	25°C Full	3.6 V	−0.1 −1		0.1 1	μA
I <sub>COM(ON)</sub>	COM ON leakage current	V <sub>NC</sub> or V <sub>NO</sub> = Open, V <sub>COM</sub> = 0 to V <sub>+</sub> ,	Switch ON, see <a href="#">Figure 10</a>	25°C Full	3.6 V	−0.1 −1		0.1 1	μA
DIGITAL INPUTS (IN12, IN2) <sup>(2)</sup>									
V <sub>IH</sub>	Input logic high			Full		V <sub>+</sub> × 0.7			V
V <sub>IL</sub>	Input logic low			Full				V <sub>+</sub> × 0.3	V
I <sub>IH</sub> , I <sub>IL</sub>	Input leakage current	V <sub>IN</sub> = 5.5 V or 0		25°C Full	3.6 V	−1 −1	0.05	1 1	μA
DYNAMIC									
t <sub>ON</sub>	Turn-on time	V <sub>NC</sub> = GND and V <sub>NO</sub> = V <sub>+</sub> or V <sub>NC</sub> = V <sub>+</sub> and V <sub>NO</sub> = GND,	R <sub>L</sub> = 500 Ω, C <sub>L</sub> = 50 pF, see <a href="#">Figure 12</a>	Full	3 V to 3.6 V	2.5		7.6	ns
t <sub>OFF</sub>	Turnoff time	V <sub>NC</sub> = GND and V <sub>NO</sub> = V <sub>+</sub> or V <sub>NC</sub> = V <sub>+</sub> and V <sub>NO</sub> = GND,	R <sub>L</sub> = 500 Ω, C <sub>L</sub> = 50 pF, see <a href="#">Figure 12</a>	Full	3 V to 3.6 V	1.5		5.3	ns
t <sub>BBM</sub>	Break-before-make time	V <sub>NC</sub> = V <sub>NO</sub> = V <sub>+</sub> /2, R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, see <a href="#">Figure 13</a>	Full	3 V to 3.6 V	0.5			ns
Q <sub>C</sub>	Charge injection	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 0.1 nF,	see <a href="#">Figure 17</a>	25°C	3.3 V		3		pC
BW	Bandwidth	R <sub>L</sub> = 50 Ω, Switch ON,	see <a href="#">Figure 14</a>	25°C	3 V		220		MHz
O <sub>ISO</sub>	OFF isolation	R <sub>L</sub> = 50 Ω, f = 10 MHz,	Switch OFF, see <a href="#">Figure 15</a>	25°C	3 V		−65		dB
X <sub>TALK</sub>	Crosstalk	R <sub>L</sub> = 50 Ω, f = 10 MHz,	Switch ON, see <a href="#">Figure 16</a>	25°C	3 V		−66		dB

(1)  $T_A = 25^\circ\text{C}$ .

(2) All unused digital inputs of the device must be held at  $V_+$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

## Electrical Characteristics for 3.3-V Supply (continued)

 $V_+ = 3\text{ V to }3.6\text{ V}$ ,  $T_A = -40^\circ\text{C to }85^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T <sub>A</sub>	V <sub>+</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
THD	Total harmonic distortion	R <sub>L</sub> = 600 Ω, C <sub>L</sub> = 50 pF,	f = 600 Hz to 20 kHz, see <a href="#">Figure 18</a>	25°C	3 V	0.015%			
SUPPLY									
I <sub>+</sub>	Positive supply current	V <sub>IN</sub> = V <sub>+</sub> or GND,	Switch ON or OFF	25°C	3.6 V	1			μA
				Full		10			
ΔI <sub>+</sub>	Change in supply current	V <sub>IN</sub> = V <sub>+</sub> – 0.6 V		Full	3.6 V	500			μA

## 6.7 Electrical Characteristics for 2.5-V Supply

 $V_+ = 2.3\text{ V to }2.7\text{ V}$ ,  $T_A = -40^\circ\text{C to }85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A$	$V_+$	MIN	TYP <sup>(1)</sup>	MAX	UNIT
<b>ANALOG SWITCH</b>							
$V_{COM}$ , $V_{NO}$ , $V_{NC}$ Analog signal range				0		$V_+$	V
$r_{on}$ ON-state resistance	$0 \leq V_{NO} \text{ or } V_{NC} \leq V_+$ , $I_{COM} = -8\text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	Full	$2.3\text{ V}$			45	$\Omega$
$\Delta r_{on}$ ON-state resistance match between channels	$V_{NO} \text{ or } V_{NC} = 1.6\text{ V}$ , $I_{COM} = -8\text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	$25^\circ\text{C}$	$2.3\text{ V}$		0.5		$\Omega$
$r_{on(Flat)}$ ON-state resistance flatness	$0 \leq V_{NO} \text{ or } V_{NC} \leq V_+$ , $I_{COM} = -8\text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	$25^\circ\text{C}$	$2.3\text{ V}$		27		$\Omega$
$I_{NC(OFF)}$ , $I_{NO(OFF)}$ NC, NO OFF leakage current	$V_{NC} \text{ or } V_{NO} = 0 \text{ to } V_+$ , $V_{COM} = 0 \text{ to } V_+$ , Switch OFF, see <a href="#">Figure 10</a>	$25^\circ\text{C}$ Full	$2.7\text{ V}$	-1 -1	0.05	1 1	$\mu\text{A}$
$I_{NC(ON)}$ , $I_{NO(ON)}$ NC, NO ON leakage current	$V_{NC} \text{ or } V_{NO} = 0 \text{ to } V_+$ , $V_{COM} = \text{Open}$ , Switch ON, see <a href="#">Figure 10</a>	$25^\circ\text{C}$ Full	$2.7\text{ V}$	-0.1 -1		0.1 1	$\mu\text{A}$
$I_{COM(ON)}$ COM ON leakage current	$V_{NC} \text{ or } V_{NO} = \text{Open}$ , $V_{COM} = 0 \text{ to } V_+$ , Switch ON, see <a href="#">Figure 10</a>	$25^\circ\text{C}$ Full	$2.7\text{ V}$	-0.1 -1		0.1 1	$\mu\text{A}$
<b>DIGITAL INPUTS (IN12, IN2)<sup>(2)</sup></b>							
$V_{IH}$ Input logic high		Full		$V_+ \times 0.7$			V
$V_{IL}$ Input logic low		Full				$V_+ \times 0.3$	V
$I_{IH}$ , $I_{IL}$ Input leakage current	$V_{IN} = 5.5\text{ V or }0$	$25^\circ\text{C}$ Full	$2.7\text{ V}$	-1 -1	0.05	1 1	$\mu\text{A}$
<b>DYNAMIC</b>							
$t_{ON}$ Turnon time	$V_{NC} = \text{GND and } V_{NO} = V_+$ or $V_{NC} = V_+ \text{ and } V_{NO} = \text{GND}$ , $R_L = 500\ \Omega$ , $C_L = 50\text{ pF}$ , see <a href="#">Figure 12</a>	Full	$2.3\text{ V to }2.7\text{ V}$	3.5		14	ns
$t_{OFF}$ Turnoff time	$V_{NC} = \text{GND and } V_{NO} = V_+$ or $V_{NC} = V_+ \text{ and } V_{NO} = \text{GND}$ , $R_L = 500\ \Omega$ , $C_L = 50\text{ pF}$ , see <a href="#">Figure 12</a>	Full	$2.3\text{ V to }2.7\text{ V}$	2		7.5	ns
$t_{BBM}$ Break-before-make time	$V_{NC} = V_{NO} = V_+/2$ , $R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$ , see <a href="#">Figure 13</a>	Full	$2.3\text{ V to }2.7\text{ V}$	0.5			ns
BW Bandwidth	$R_L = 50\ \Omega$ , Switch ON, see <a href="#">Figure 14</a>	$25^\circ\text{C}$	$2.3\text{ V}$		220		MHz
$O_{ISO}$ OFF isolation	$R_L = 50\ \Omega$ , $f = 10\text{ MHz}$ , Switch OFF, see <a href="#">Figure 15</a>	$25^\circ\text{C}$	$2.3\text{ V}$		-65		dB

(1)  $T_A = 25^\circ\text{C}$ .

(2) All unused digital inputs of the device must be held at  $V_+$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

## Electrical Characteristics for 2.5-V Supply (continued)

 $V_+ = 2.3 \text{ V to } 2.7 \text{ V}$ ,  $T_A = -40^\circ\text{C to } 85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A$	$V_+$	MIN	TYP <sup>(1)</sup>	MAX	UNIT
$X_{\text{TALK}}$ Crosstalk	$R_L = 50 \Omega$ , $f = 10 \text{ MHz}$ , Switch ON, see <a href="#">Figure 16</a>	$25^\circ\text{C}$	2.3 V		–66		dB
THD Total harmonic distortion	$R_L = 600 \Omega$ , $C_L = 50 \text{ pF}$ , $f = 600 \text{ Hz to } 20 \text{ kHz}$ , see <a href="#">Figure 18</a>	$25^\circ\text{C}$	2.3 V		0.025%		
<b>SUPPLY</b>							
$I_+$ Positive supply current	$V_{\text{IN}} = V_+$ or GND, Switch ON or OFF	$25^\circ\text{C}$ Full	2.7 V			1 10	$\mu\text{A}$
$\Delta I_+$ Change in supply current	$V_{\text{IN}} = V_+ - 0.6 \text{ V}$	Full	2.7 V			500	$\mu\text{A}$

## 6.8 Electrical Characteristics for 1.8-V Supply

 $V_+ = 1.65 \text{ V to } 1.95 \text{ V}$ ,  $T_A = -40^\circ\text{C to } 85^\circ\text{C}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A$	$V_+$	MIN	TYP <sup>(1)</sup>	MAX	UNIT
<b>ANALOG SWITCH</b>							
$V_{\text{COM}}$ , $V_{\text{NO}}$ , $V_{\text{NC}}$ Analog signal range				0		$V_+$	V
$r_{\text{on}}$ ON-state resistance	$0 \leq V_{\text{NO}} \text{ or } V_{\text{NC}} \leq V_+$ , $I_{\text{COM}} = -4 \text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	Full	1.65 V			140	$\Omega$
$\Delta r_{\text{on}}$ ON-state resistance match between channels	$V_{\text{NO}} \text{ or } V_{\text{NC}} = 1.15 \text{ V}$ , $I_{\text{COM}} = -4 \text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	$25^\circ\text{C}$	1.65 V		1		$\Omega$
$r_{\text{on(flat)}}$ ON-state resistance flatness	$0 \leq V_{\text{NO}} \text{ or } V_{\text{NC}} \leq V_+$ , $I_{\text{COM}} = -4 \text{ mA}$ , Switch ON, see <a href="#">Figure 9</a>	$25^\circ\text{C}$	1.65 V		110		$\Omega$
$I_{\text{NC(OFF)}}$ , NC, NO $I_{\text{NO(OFF)}}$ OFF leakage current	$V_{\text{NC}} \text{ or } V_{\text{NO}} = 0 \text{ to } V_+$ , $V_{\text{COM}} = 0 \text{ to } V_+$ , Switch OFF, see <a href="#">Figure 10</a>	$25^\circ\text{C}$ Full	1.95 V	–1	0.05	1	$\mu\text{A}$
$I_{\text{NC(ON)}}$ , NC, NO $I_{\text{NO(ON)}}$ ON leakage current	$V_{\text{NC}} \text{ or } V_{\text{NO}} = 0 \text{ to } V_+$ , $V_{\text{COM}} = \text{Open}$ , Switch ON, see <a href="#">Figure 10</a>	$25^\circ\text{C}$ Full	1.95 V	–0.1		0.1	$\mu\text{A}$
$I_{\text{COM(ON)}}$ COM ON leakage current	$V_{\text{NC}} \text{ or } V_{\text{NO}} = \text{Open}$ , $V_{\text{COM}} = 0 \text{ to } V_+$ , Switch ON, see <a href="#">Figure 10</a>	$25^\circ\text{C}$ Full	1.95 V	–0.1		0.1	$\mu\text{A}$
<b>DIGITAL INPUTS (IN12, IN2)<sup>(2)</sup></b>							
$V_{\text{IH}}$ Input logic high		Full		$V_+ \times 0.75$			V
$V_{\text{IL}}$ Input logic low		Full				$V_+ \times 0.25$	V
$I_{\text{IH}}$ , $I_{\text{IL}}$ Input leakage current	$V_{\text{IN}} = 5.5 \text{ V or } 0$	$25^\circ\text{C}$ Full	1.95 V	–1	0.05	1	$\mu\text{A}$
<b>DYNAMIC</b>							
$t_{\text{ON}}$ Turnon time	$V_{\text{NC}} = \text{GND}$ and $V_{\text{NO}} = V_+$ , or $V_{\text{NC}} = V_+$ and $V_{\text{NO}} = \text{GND}$ , $R_L = 500 \Omega$ , $C_L = 50 \text{ pF}$ , see <a href="#">Figure 12</a>	Full	1.65 V to 1.95 V	7		24	ns
$t_{\text{OFF}}$ Turnoff time	$V_{\text{NC}} = \text{GND}$ and $V_{\text{NO}} = V_+$ , or $V_{\text{NC}} = V_+$ and $V_{\text{NO}} = \text{GND}$ , $R_L = 500 \Omega$ , $C_L = 50 \text{ pF}$ , see <a href="#">Figure 12</a>	Full	1.65 V to 1.95 V	3		13	ns
$t_{\text{BBM}}$ Break-before-make time	$V_{\text{NC}} = V_{\text{NO}} = V_+/2$ , $R_L = 50 \Omega$ , $C_L = 35 \text{ pF}$ , see <a href="#">Figure 13</a>	Full	1.65 V to 1.95 V	0.5			ns
BW Bandwidth	$R_L = 50 \Omega$ , Switch ON, see <a href="#">Figure 14</a>	$25^\circ\text{C}$	1.8 V		220		MHz

(1)  $T_A = 25^\circ\text{C}$ .

(2) All unused digital inputs of the device must be held at  $V_+$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).



## Electrical Characteristics for 1.8-V Supply (continued)

 $V_+ = 1.65\text{ V to }1.95\text{ V}$ ,  $T_A = -40^\circ\text{C to }85^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS		$T_A$	$V_+$	MIN	TYP <sup>(1)</sup>	MAX	UNIT
$O_{ISO}$	OFF isolation	$R_L = 50\ \Omega$ , $f = 10\text{ MHz}$ ,	Switch OFF, see <a href="#">Figure 15</a>	$25^\circ\text{C}$	1.8 V		–60		dB
$X_{TALK}$	Crosstalk	$R_L = 50\ \Omega$ , $f = 10\text{ MHz}$ ,	Switch ON, see <a href="#">Figure 16</a>	$25^\circ\text{C}$	1.8 V		–66		dB
THD	Total harmonic distortion	$R_L = 600\ \Omega$ , $C_L = 50\text{ pF}$ ,	$f = 600\text{ Hz to }20\text{ kHz}$ , see <a href="#">Figure 18</a>	$25^\circ\text{C}$	1.8 V		0.015%		
<b>SUPPLY</b>									
$I_+$	Positive supply current	$V_{IN} = V_+ \text{ or GND}$ ,	Switch ON or OFF	$25^\circ\text{C}$	1.95 V			1	$\mu\text{A}$
				Full				10	
$\Delta I_+$	Change in supply current	$V_{IN} = V_+ - 0.6\text{ V}$		Full	1.95 V			500	$\mu\text{A}$

## 6.9 Typical Characteristics

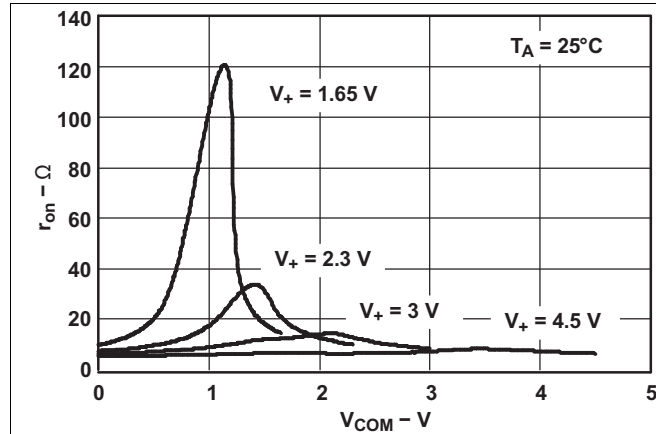


Figure 1.  $r_{on}$  vs  $V_{COM}$

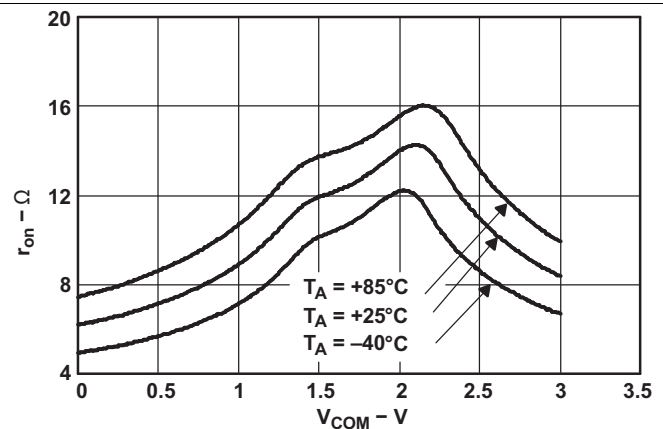


Figure 2.  $r_{on}$  vs  $V_{COM}$  ( $V_+ = 3$  V)

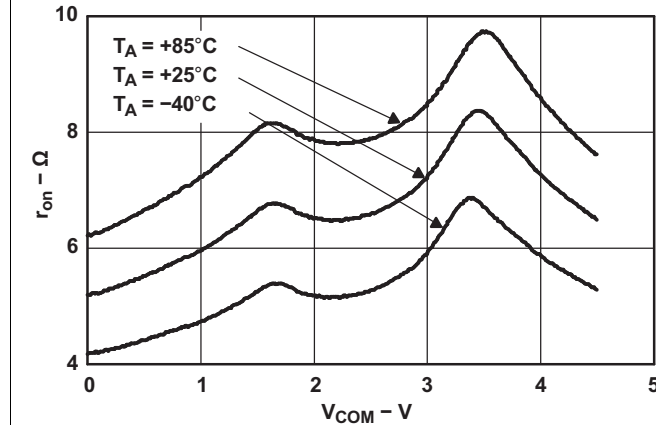


Figure 3.  $r_{on}$  vs  $V_{COM}$  ( $V_+ = 5$  V)

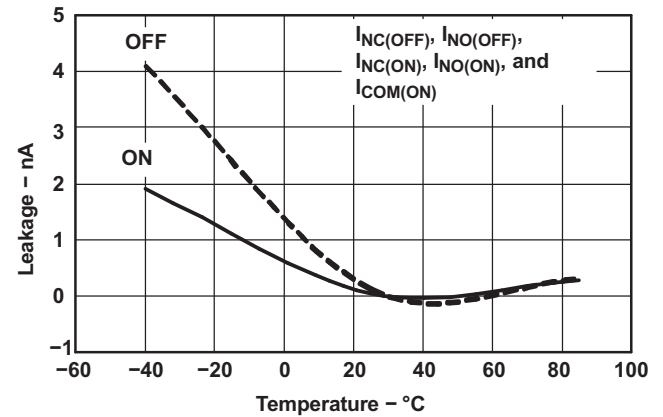


Figure 4. Leakage Current vs Temperature ( $V_+ = 5.5$  V)

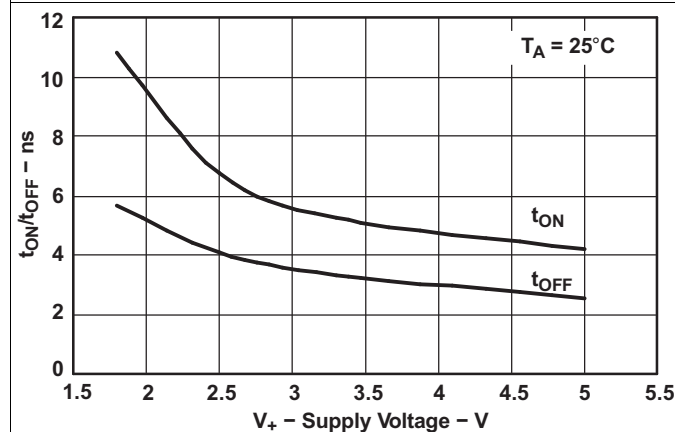


Figure 5.  $t_{ON}$  and  $t_{OFF}$  vs  $V_+$

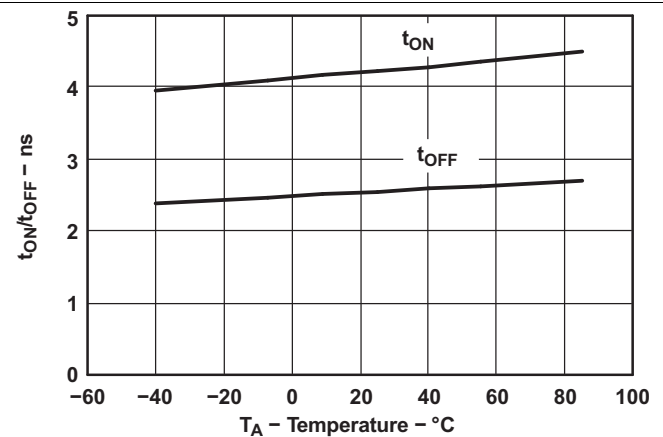


Figure 6.  $t_{ON}$  and  $t_{OFF}$  vs Temperature ( $V_+ = 5$  V)

## Typical Characteristics (continued)

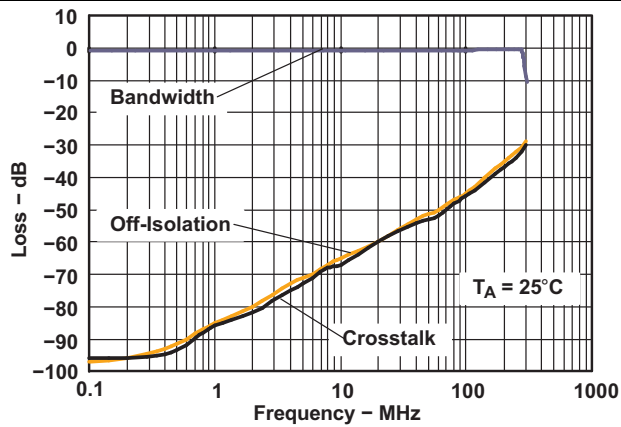


Figure 7. Frequency Response ( $V_+ = 3\text{ V}$ )

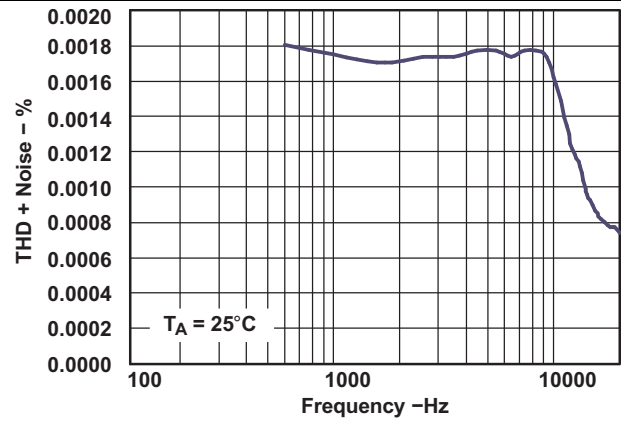
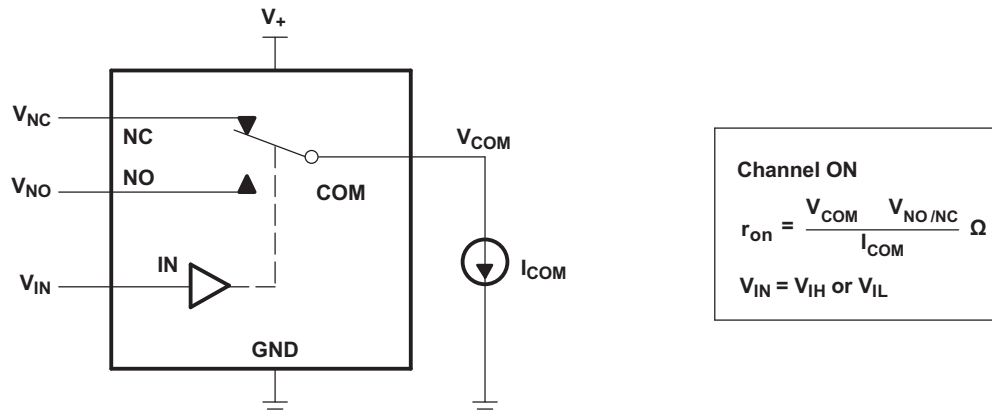
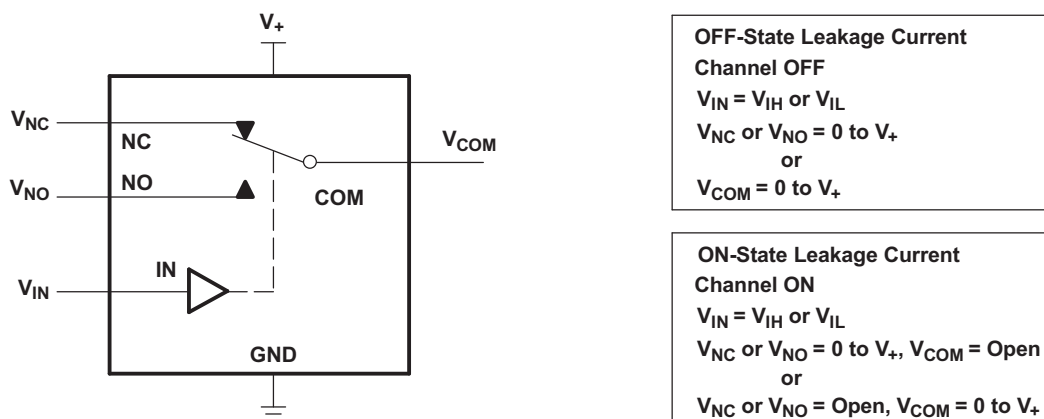


Figure 8. Total Harmonic Distortion (THD) vs Frequency ( $V_+ = 3\text{ V}$ )

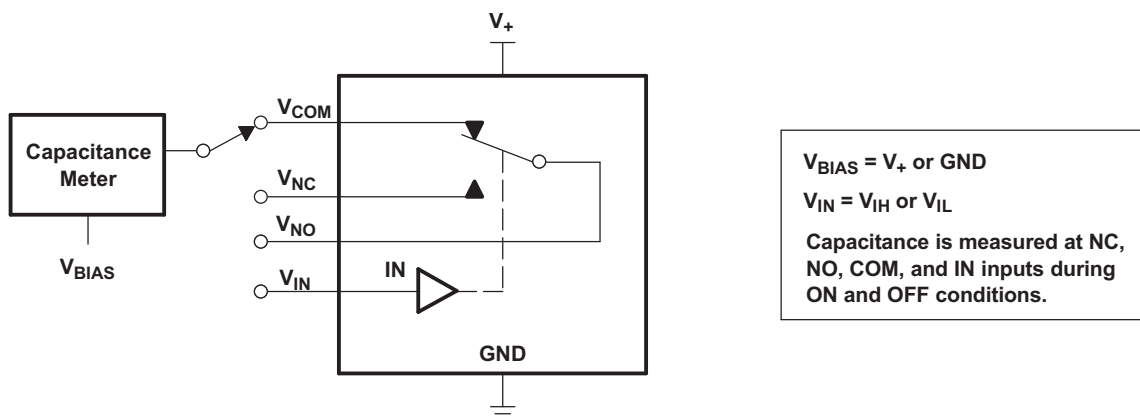
## 7 Parameter Measurement Information



**Figure 9. ON-State Resistance ( $r_{on}$ )**



**Figure 10. ON- and OFF-State Leakage Current ( $I_{COM(ON)}$ ,  $I_{NC(OFF)}$ ,  $I_{NO(OFF)}$ ,  $I_{NC(ON)}$ ,  $I_{NO(ON)}$ )**



**Figure 11. Capacitance ( $C_{IN}$ ,  $C_{COM(ON)}$ ,  $C_{NC(OFF)}$ ,  $C_{NO(OFF)}$ ,  $C_{NC(ON)}$ ,  $C_{NO(ON)}$ )**

## Parameter Measurement Information (continued)

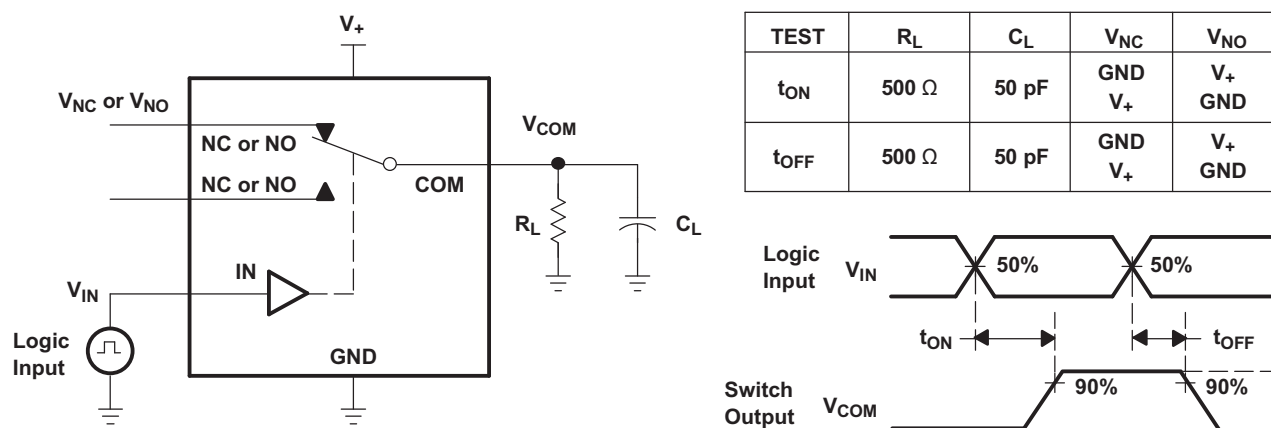


Figure 12. Turnon ( $t_{ON}$ ) and Turnoff ( $t_{OFF}$ ) Time

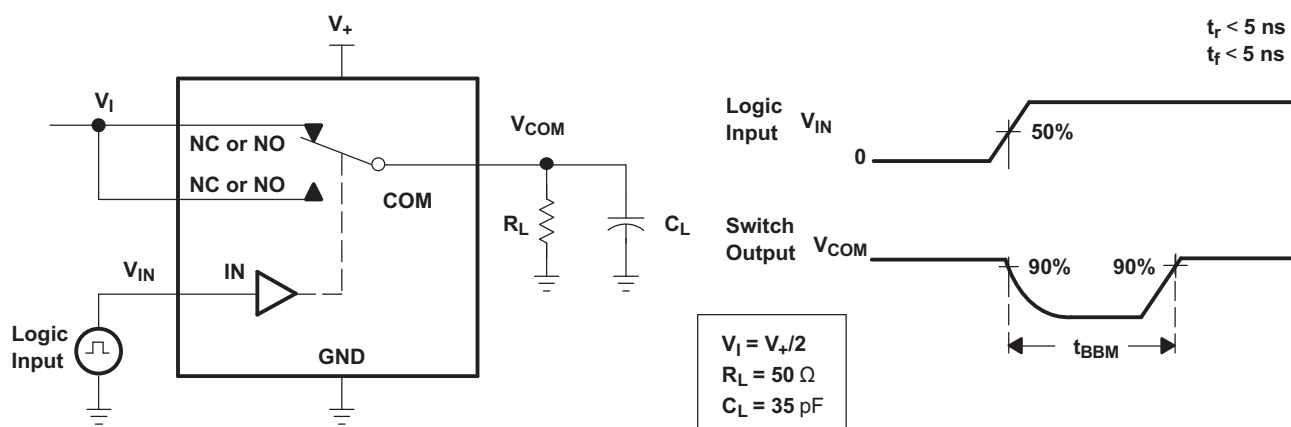


Figure 13. Break-Before-Make ( $t_{BBM}$ ) Time

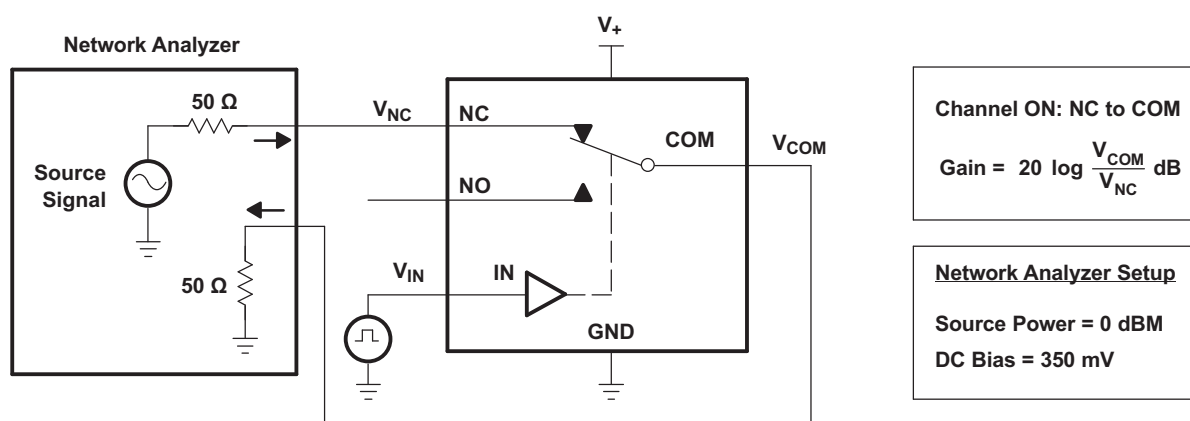
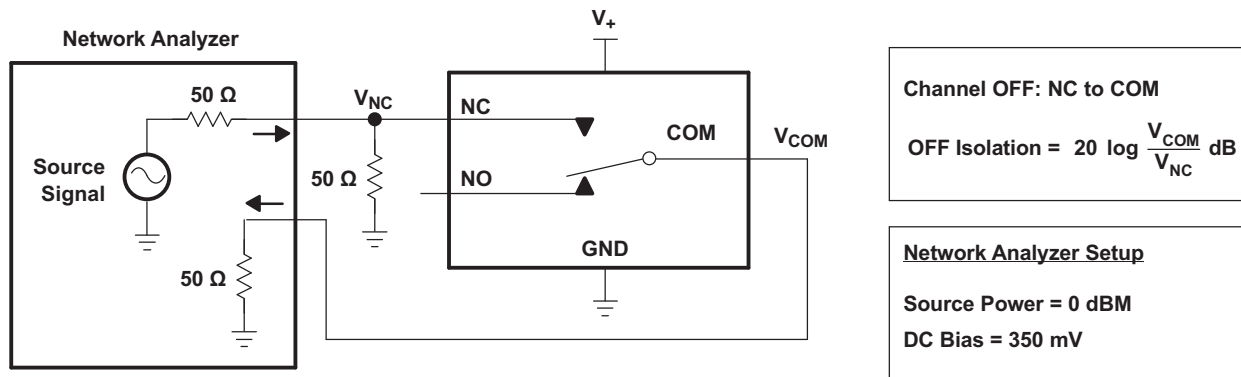
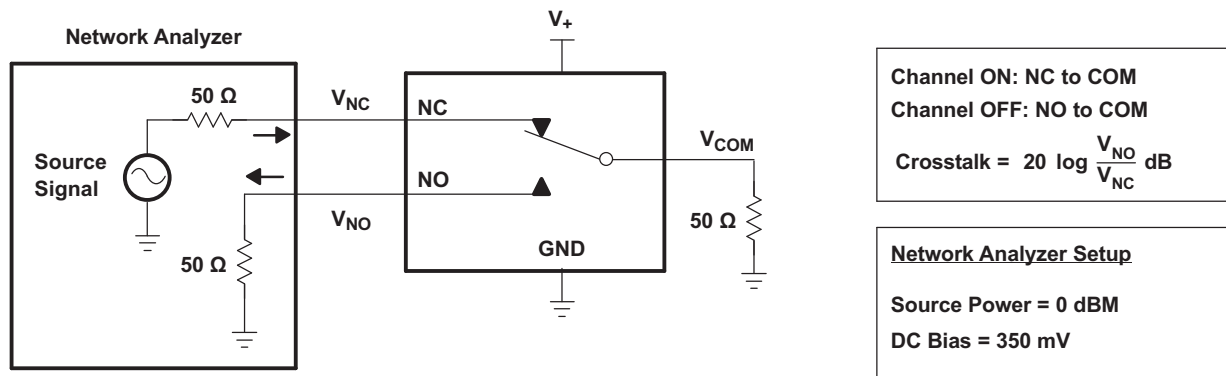
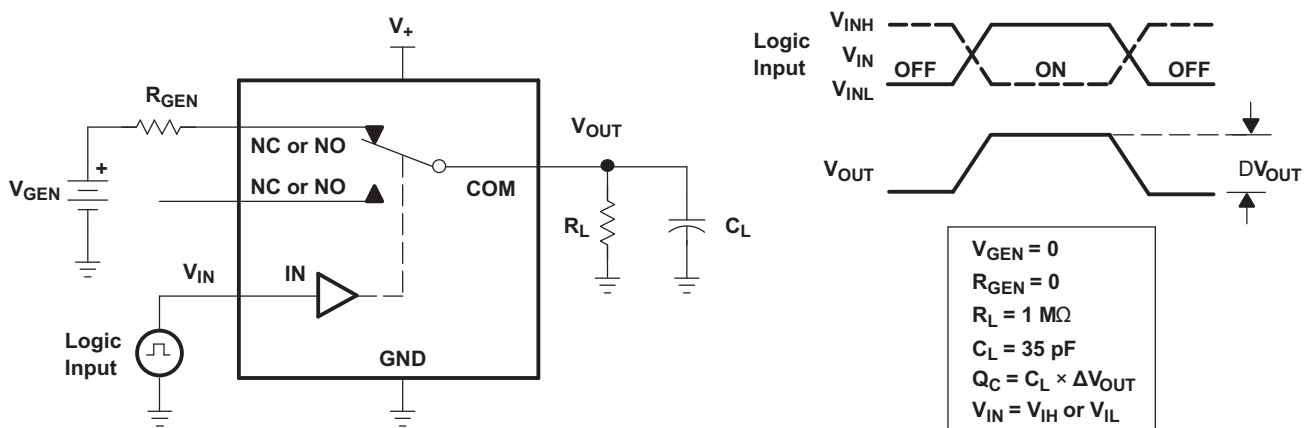


Figure 14. Frequency Response (BW)

## Parameter Measurement Information (continued)


**Figure 15. OFF Isolation ( $O_{ISO}$ )**

**Figure 16. Crosstalk ( $X_{TALK}$ )**

**Figure 17. Charge Injection ( $Q_C$ )**

Channel ON: COM to NC  
 $V_{SOURCE} = 0.5 \text{ V P-P}$   
 $f_{SOURCE} = 600 \text{ Hz to } 20 \text{ kHz}$   
 $R_L = 600 \Omega$   
 $C_L = 50 \text{ pF}$

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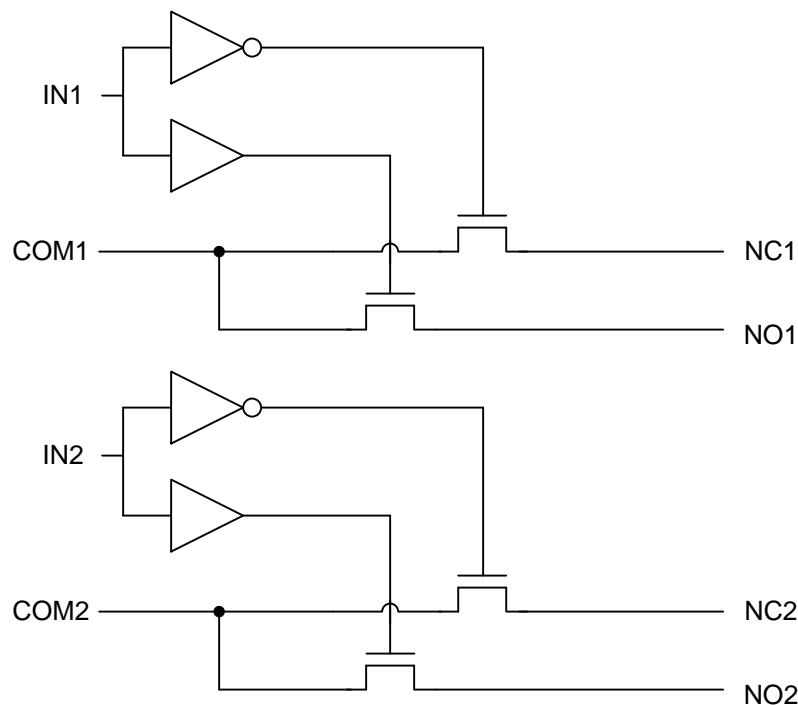
## 8 Detailed Description

### 8.1 Overview

The TS5A23157 is a dual single-pole-double-throw (SPDT) solid-state analog switch. The TS5A23157, like all analog switches, is bidirectional. When powered on, each COM pin is connected to its respective NC pin when the IN pin is low. For this device, NC stands for *normally closed* and NO stands for *normally open*. If IN is low, COM is connected to NC. If IN is high, COM is connected to NO.

The TS5A23157 is a break-before-make switch. This means that during switching, a connection is broken before a new connection is established. The NC and NO pins are never connected to each other.

### 8.2 Functional Block Diagram



### 8.3 Feature Description

The low ON-state resistance, ON-state resistance matching, and charge injection in the TS5A23157 make this switch an excellent choice for analog signals that require minimal distortion. In addition, the low THD allows audio signals to be preserved more clearly as they pass through the device.

The 1.65-V to 5.5-V operation allows compatibility with more logic levels, and the bidirectional I/Os can pass analog signals from 0 V to  $V_+$  with low distortion. The control inputs are 5-V tolerant, allowing control signals to be present without  $V_{CC}$ .

### 8.4 Device Functional Modes

Table 1 lists the functional modes for TS5A23157.

**Table 1. Function Table**

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON



## 9 Application and Implementation

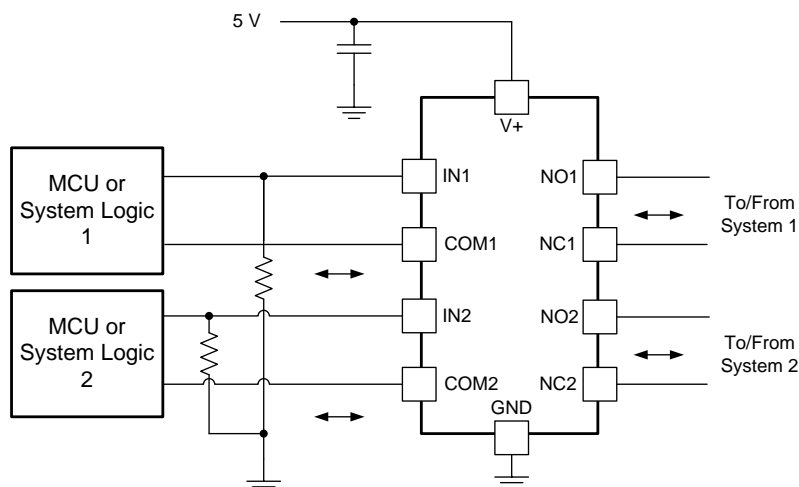
### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

The TS5A3157 can be used in a variety of customer systems. The TS5A3157 can be used anywhere multiple analog or digital signals must be selected to pass across a single line.

### 9.2 Typical Application



**Figure 19. System Schematic for TS5A23157**

#### 9.2.1 Design Requirements

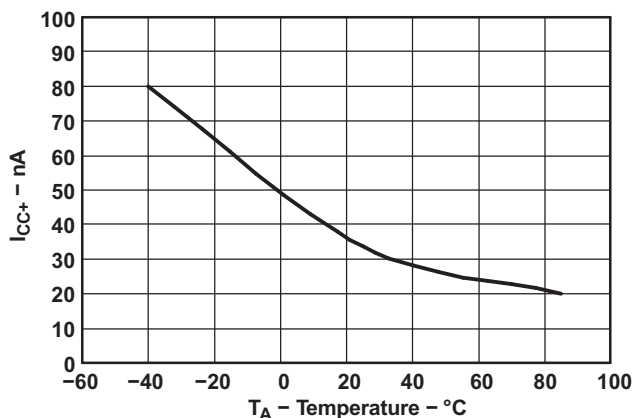
In this particular application,  $V_+$  was 5 V, although  $V_+$  is allowed to be any voltage specified in [Recommended Operating Conditions](#). A decoupling capacitor is recommended on the  $V_+$  pin. See [Power Supply Recommendations](#) for more details.

#### 9.2.2 Detailed Design Procedure

In this application, IN is, by default, pulled low to GND. Choose the resistor size based on the current driving strength of the GPIO, the desired power consumption, and the switching frequency (if applicable). If the GPIO is open-drain, use pullup resistors instead.

## Typical Application (continued)

### 9.2.3 Application Curve



**Figure 20. Power-Supply Current vs Temperature ( $V_+ = 5\text{ V}$ )**

## 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [Recommended Operating Conditions](#).

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu\text{F}$  bypass capacitor is recommended. If there are multiple pins labeled  $V_{CC}$ , then a 0.01- $\mu\text{F}$  or 0.022- $\mu\text{F}$  capacitor is recommended for each  $V_{CC}$  because the  $V_{CC}$  pins will be tied together internally. For devices with dual supply pins operating at different voltages, for example  $V_{CC}$  and  $V_{DD}$ , a 0.1- $\mu\text{F}$  bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- $\mu\text{F}$  and 1- $\mu\text{F}$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

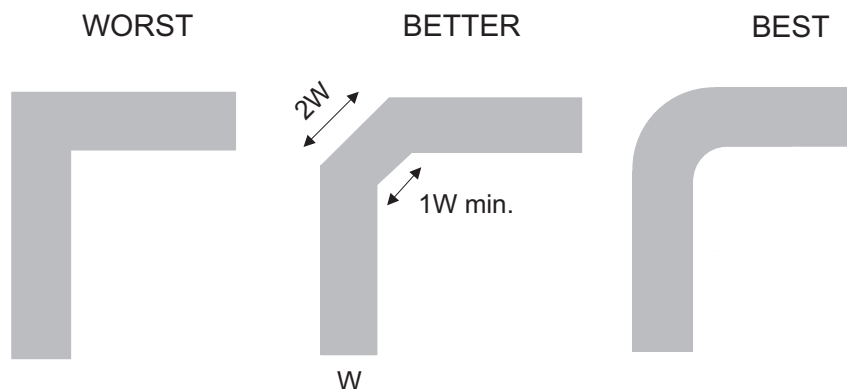
## 11 Layout

### 11.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant their own discussion. When a PCB trace turns a corner at a 90° angle, a reflection can occur. This is primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times its width. This upsets the transmission line characteristics, especially the distributed capacitance and self-inductance of the trace — resulting in the reflection. It is a given that not all PCB traces can be straight, and so they will have to turn corners. Below figure shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.

Unused switch I/Os, such as NO, NC, and COM, can be left floating or tied to GND. However, the IN pin must be driven high or low. Due to partial transistor turnon when control inputs are at threshold levels, floating control inputs can cause increased  $I_{CC}$  or unknown switch selection states.

## 11.2 Layout Example



**Figure 21. Trace Example**

## 12 Device and Documentation Support

### 12.1 Device Support

#### 12.1.1 Device Nomenclature

**Table 2. Parameter Description**

SYMBOL	DESCRIPTION
$V_{COM}$	Voltage at COM
$V_{NC}$	Voltage at NC
$V_{NO}$	Voltage at NO
$r_{on}$	Resistance between COM and NC or COM and NO ports when the channel is ON
$\Delta r_{on}$	Difference of $r_{on}$ between channels
$r_{on(flat)}$	Difference between the maximum and minimum value of $r_{on}$ in a channel over the specified range of conditions
$I_{NC(OFF)}$	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions
$I_{NO(OFF)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions
$I_{NC(ON)}$	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) being open
$I_{NO(ON)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) being open
$I_{COM(ON)}$	Leakage current measured at the COM port, with the corresponding channel (NO to COM or NC to COM) in the ON state and the output (NC or NO) being open
$V_{IH}$	Minimum input voltage for logic high for the control input (IN)
$V_{IL}$	Minimum input voltage for logic low for the control input (IN)
$V_{IN}$	Voltage at IN
$I_{IH}, I_{IL}$	Leakage current measured at IN
$t_{ON}$	Turnon time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog outputs (COM/NC/NO) signal when the switch is turning ON.
$t_{OFF}$	Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog outputs (COM/NC/NO) signal when the switch is turning OFF.
$t_{BBM}$	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.

**Table 2. Parameter Description (continued)**

SYMBOL	DESCRIPTION
$Q_C$	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulombs (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_O$ , $C_L$ is the load capacitance and $\Delta V_O$ is the change in analog output voltage.
$C_{NC(OFF)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NC to COM) is OFF
$C_{NC(ON)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
$C_{NO(ON)}$	Capacitance at the NO port when the corresponding channel (NC to COM) is ON
$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON
$C_{IN}$	Capacitance of IN
$O_{ISO}$	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. OFF isolation, $O_{ISO} = 20 \log (V_{NC}/V_{COM})$ dB, $V_{COM}$ is the input and $V_{NC}$ is the output.
$X_{TALK}$	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured at a specific frequency and in dB. Crosstalk, $X_{TALK} = 20 \log (V_{NC1}/V_{NO1})$ , $V_{NO1}$ is the input and $V_{NC1}$ is the output.
BW	Bandwidth of the switch. This is the frequency where the gain of an ON channel is –3 dB below the dc gain. Gain is measured from the equation, $20 \log (V_{NC}/V_{COM})$ dB, where $V_{NC}$ is the output and $V_{COM}$ is the input.
$I_+$	Static power-supply current with the control (IN) pin at $V_+$ or GND
$\Delta I_+$	This is the increase in $I_+$ for each control (IN) input that is at the specified voltage, rather than at $V_+$ or GND.

**Table 3. Summary of Characteristics**

CONFIGURATION	2:1 MULTIPLEXER/DEMUTIPLEXER (2 × SPDT)
Number of channels	2
ON-state resistance ( $r_{on}$ )	10 $\Omega$
ON-state resistance match between channels ( $\Delta r_{on}$ )	0.15 $\Omega$
ON-state resistance flatness ( $r_{on(flat)}$ )	4 $\Omega$
Turnon/turnoff time ( $t_{ON}/t_{OFF}$ )	5.7 ns/3.8 ns
Break-before-make time ( $t_{BBM}$ )	0.5 ns
Charge injection ( $Q_C$ )	7 pC
Bandwidth (BW)	220 MHz
OFF isolation ( $O_{SIO}$ )	–65 dB at 10 MHz
Crosstalk 9XTALK)	–66 dB at 10 MHz
Total harmonic distortion (THD)	0.01%
Leakage current ( $I_{COM(OFF)}/I_{NC(OFF)}$ )	$\pm 1 \mu A$
Package options	10-pin DGS and RSE

## 12.2 Documentation Support

### 12.2.1 Related Documentation

For related documentation, see the following:

- *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#)

## 12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](#), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

## 12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

## 12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A23157DGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	<a href="#">Samples</a>
TS5A23157DGSRE4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	<a href="#">Samples</a>
TS5A23157DGSRG4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	<a href="#">Samples</a>
TS5A23157DGST	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	<a href="#">Samples</a>
TS5A23157DGSTG4	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	<a href="#">Samples</a>
TS5A23157RSER	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBO	<a href="#">Samples</a>
TS5A23157RSE4	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBO	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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**OTHER QUALIFIED VERSIONS OF TS5A23157 :**

- Automotive: [TS5A23157-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A23157DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS5A23157DGST	VSSOP	DGS	10	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS5A23157RSER	UQFN	RSE	10	3000	179.0	8.4	1.75	2.25	0.65	4.0	8.0	Q1



## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A23157DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0
TS5A23157DGST	VSSOP	DGS	10	250	358.0	335.0	35.0
TS5A23157RSER	UQFN	RSE	10	3000	203.0	203.0	35.0

## DGS (S-PDSO-G10)

## PLASTIC SMALL-OUTLINE PACKAGE

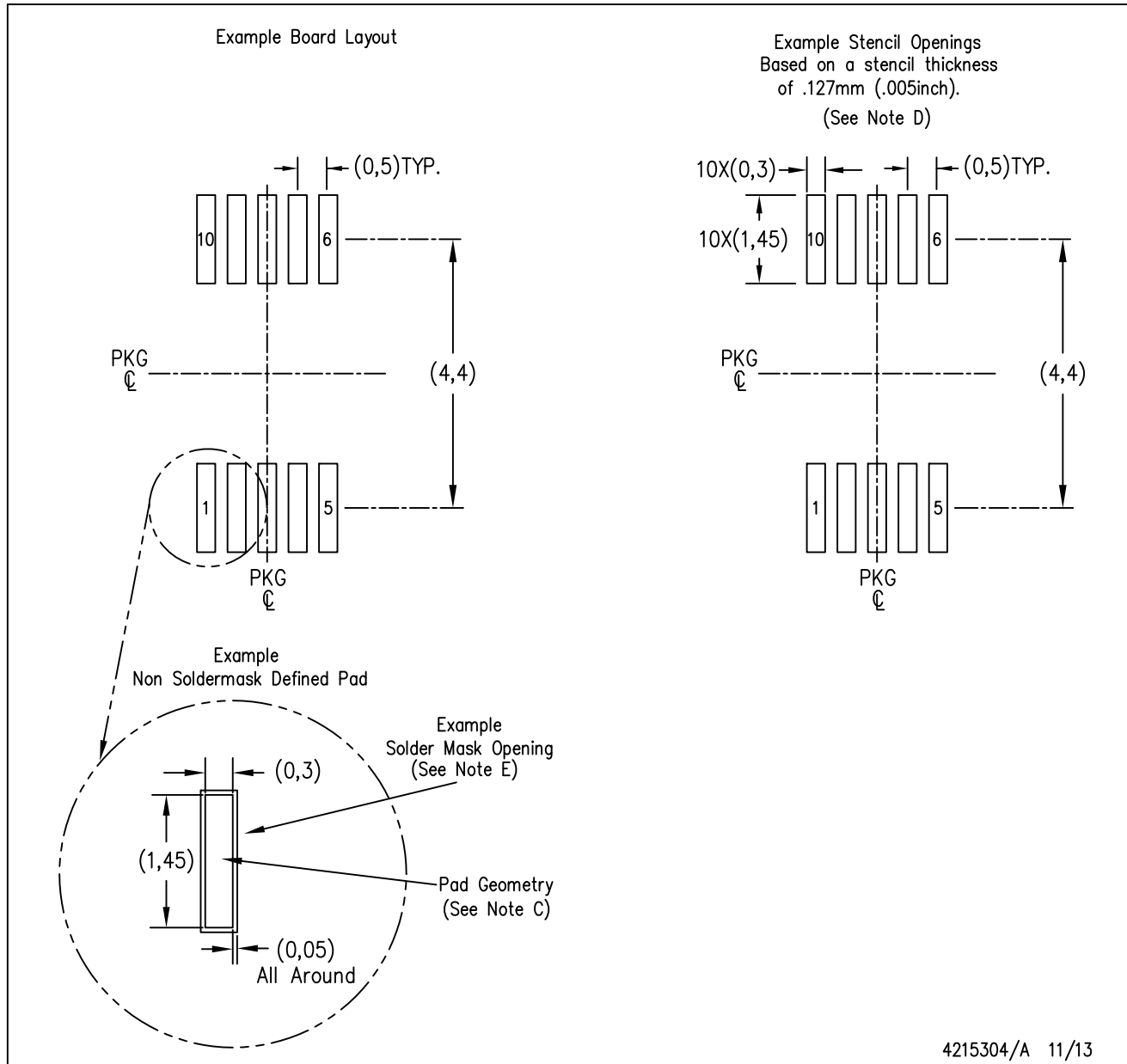


4073272/C 02/04

- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Body dimensions do not include mold flash or protrusion.
  - Falls within JEDEC MO-187 variation BA.

DGS (S-PDSO-G10)

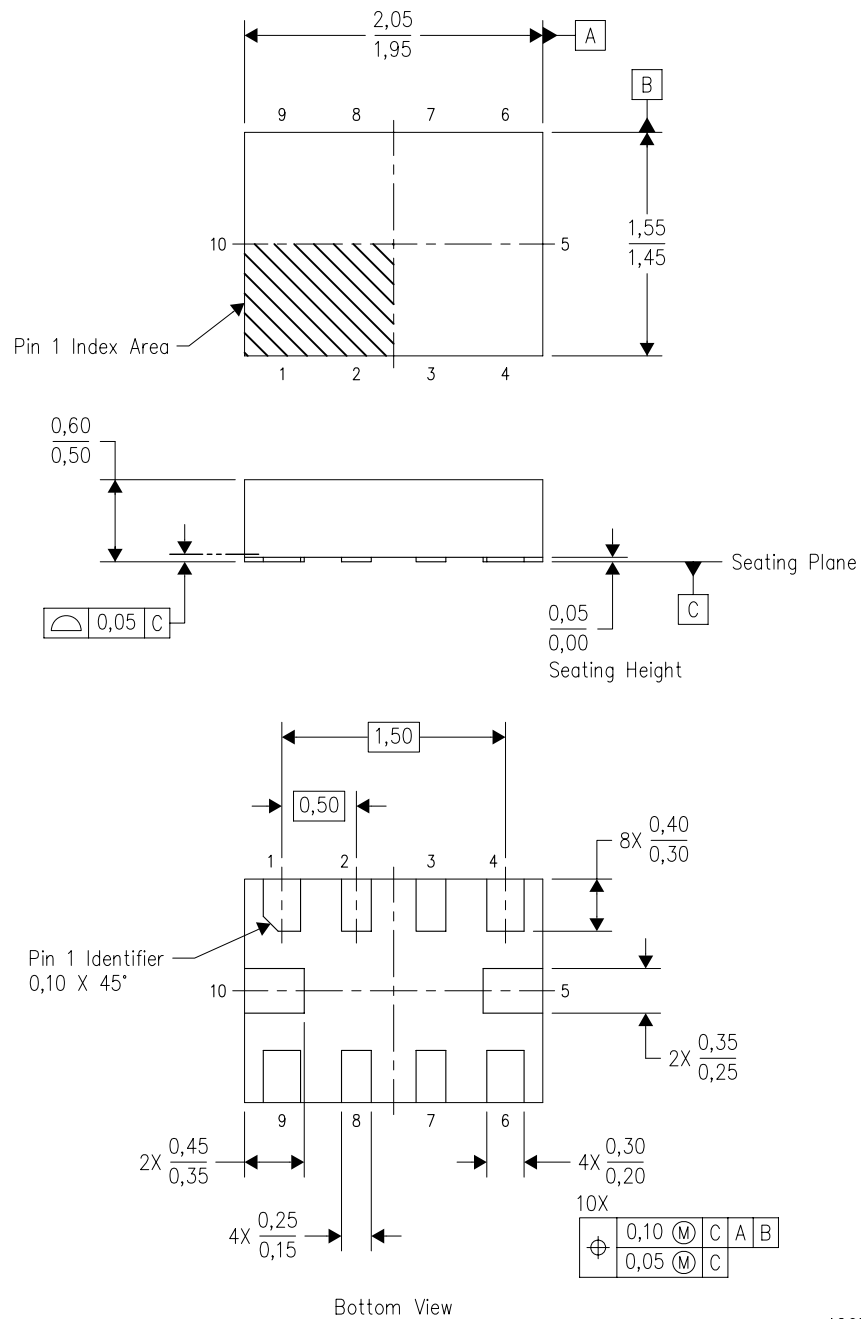
PLASTIC SMALL OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

RSE (R-PUQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD

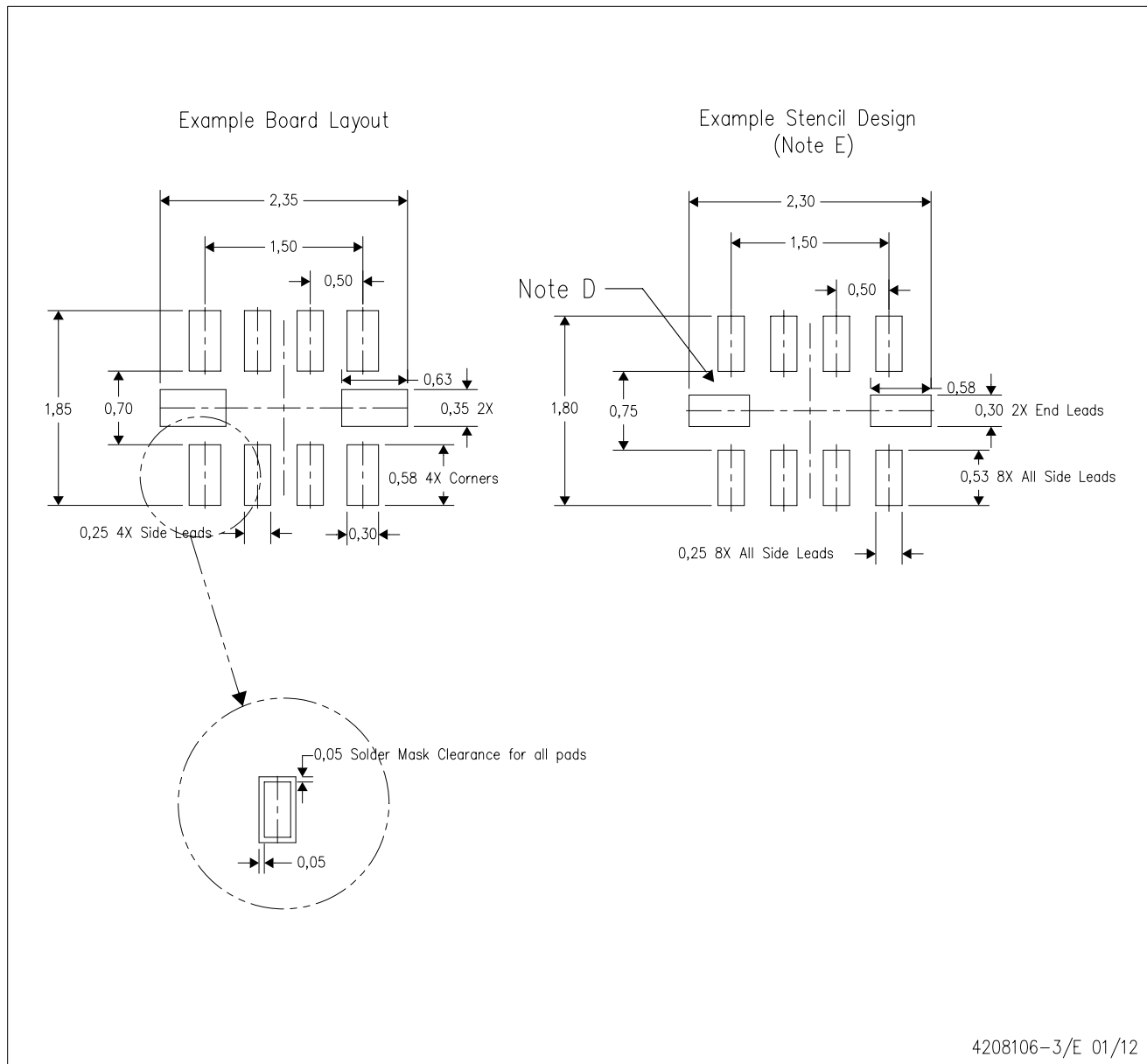


4207268-3/D 01/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. QFN (Quad Flatpack No-Lead) package configuration.
  - D. This package complies to JEDEC MO-288 variation UEFD.

RSE (R-PUQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
  - E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
  - F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
  - G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.

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